

# Octal Buffer/Line Driver with 3-State Outputs 74AC541, 74ACT541

# **General Description**

The 74AC541 and 74ACT541 are octal buffer/line drivers designed to be employed as memory and address drivers, clock drivers and bus oriented transmitter/receivers.

These devices are similar in function to the 74AC244 and 74ACTC244 while providing flow–through architecture (inputs on opposite side from outputs). This pinout arrangement makes these devices especially useful as an output port for microprocessors, allowing ease of layout and greater PC board density.

#### **Features**

- I<sub>CC</sub> and I<sub>OZ</sub> Reduced by 50%
- 3-State Outputs
- Inputs and Outputs Opposite Side of Package, allowing easier Interface to Microprocessors
- Outputs Source/Sink 24 mA
- 74AC541 is a Non-inverting Option of the 74AC540
- 74ACT541 has TTL-compatible Inputs
- These are Pb-Free Devices

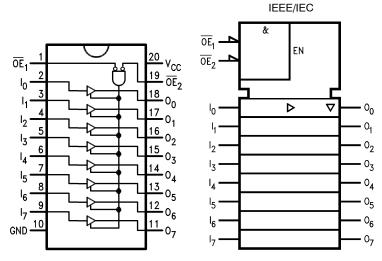


Figure 1. Connection Diagram

Figure 2. Logic Symbol

1

#### **TRUTH TABLE**

	Inputs		
OE <sub>1</sub>	OE <sub>2</sub>	I	Outputs
L	L	Н	Н
Н	Χ	Χ	Z
X	Н	Χ	Z
L	L	L	L

H = HIGH Voltage Level

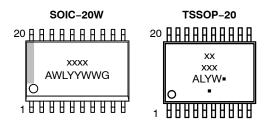
L = LOW Voltage Level

X = Immaterial

Z = High Impedance



#### **MARKING DIAGRAMS**



xxxx = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package
(Note: Microdot may be in either location)

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Rating	Unit
V <sub>CC</sub>	Supply Voltage	−0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current $V_{I} = -0.5 \text{ V}$ $V_{I} = V_{CC} + 0.5 \text{ V}$	-20 +20	mA
VI	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>OK</sub>	DC Output Diode Current $V_O = -0.5 \text{ V}$ $V_O = V_{CC} + 0.5 \text{ V}$	-20 +20	mA
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>O</sub>	DC Output Source or Sink Current	±50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current per Output Pin	±50	mA
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
TJ	Junction Temperature	140	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Supply Voltage AC ACT	2.0 4.5	6.0 5.5	V
V <sub>I</sub>	Input Voltage	0	V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature	-40	85	°C
ΔV/Δt	Minimum Input Edge Rate, AC Devices: V <sub>IN</sub> from 30% to 70% V <sub>CC,</sub> V <sub>CC</sub> @ 3.3 V, 4.5 V, 5.5 V	125		mV/ns
ΔV/Δt	Minimum Input Edge Rate, ACT Devices: V <sub>IN</sub> from 0.8 V to 2.0 V, V <sub>CC</sub> @ 4.5 V, 5.5 V	125		mV/ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS FOR AC

				T <sub>A</sub> = +	-25°C	T <sub>A</sub> = -40°C to +85°C	
Symbol	Parameter	V <sub>CC</sub> (V)	Conditions	Тур.	G	iuaranteed Limits	Units
$V_{IH}$	Minimum HIGH Level	3.0	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	1.5	2.1	2.1	٧
	Input Voltage	4.5	1	2.25	3.15	3.15	1
		5.5		2.75	3.85	3.85	
$V_{IL}$	Maximum LOW Level	3.0	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	1.5	0.9	0.9	٧
	Input Voltage	4.5	1	2.25	1.35	1.35	1
		5.5		2.75	1.65	1.65	
V <sub>OH</sub>	Minimum HIGH Level	3.0	I <sub>OUT</sub> = -50 μA	2.99	2.9	2.9	V
	Output Voltage	4.5		4.49	4.4	4.4	1
		5.5	1	5.49	5.4	5.4	1
		3.0	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OH} = -12$ mA		2.56	2.46	
		4.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OH} = -24$ mA		3.86	3.76	1
		5.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OH} = -24$ mA <sup>(1)</sup>		4.86	4.76	1
V <sub>OL</sub>	Maximum LOW Level	3.0	I <sub>OUT</sub> = 50 μA	0.002	0.1	0.1	V
	Output Voltage	4.5		0.001	0.1	0.1	1
		5.5		0.001	0.1	0.1	1
		3.0	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OL} = 12$ mA		0.36	0.44	
		4.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OL} = 24$ mA		0.36	0.44	1
		5.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OL} = 24$ mA <sup>(1)</sup>		0.36	0.44	1
I <sub>IN</sub> (Note 2)	Maximum Input Leakage Current	5.5	$V_I = V_{CC}$ , GND		±0.1	±1.0	μΑ
l <sub>OZ</sub>	Maximum 3-STATE Leakage Current	5.5	$\begin{aligned} &V_{l}\left(OE\right)=V_{lL},V_{lH};V_{l}=V_{CC},GND;\\ &V_{O}=V_{CC},GND \end{aligned}$		±0.25	±2.5	μΑ
I <sub>OLD</sub>	Minimum Dynamic	5.5	V <sub>OLD</sub> = 1.65 V Max.			75	mA
I <sub>OHD</sub>	Output Current (Note 3)	5.5	V <sub>OHD</sub> = 3.85 V Min.			-75	mA
I <sub>CC</sub> (Note 2)	Maximum Quiescent Supply Current	5.5	V <sub>IN</sub> = V <sub>CC</sub> or GND		4.0	40.0	μΑ

All outputs loaded; thresholds on input associated with output under test.
 I<sub>IN</sub> and I<sub>CC</sub> @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V<sub>CC</sub>.
 Maximum test duration 2.0 ms, one output loaded at a time.

# DC ELECTRICAL CHARACTERISTICS FOR ACT

				T <sub>A</sub> = +	+25°C	T <sub>A</sub> = -40°C to +85°C	
Symbol	Parameter	V <sub>CC</sub> (V)	Conditions	Тур.	G	iuaranteed Limits	Units
$V_{IH}$	Minimum HIGH Level	4.5	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	1.5	2.0	2.0	٧
	Input Voltage	5.5		1.5	2.0	2.0	
$V_{IL}$	Maximum LOW Level	4.5	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	1.5	0.8	0.8	٧
	Input Voltage	5.5		1.5	0.8	0.8	
V <sub>OH</sub>	Minimum HIGH Level	4.5	I <sub>OUT</sub> = -50 μA	4.49	4.4	4.4	٧
	Output Voltage	5.5		5.49	5.4	5.4	
		4.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OH} = -24$ mA		3.86	3.76	
		5.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OH} = -24$ mA <sup>(4)</sup>		4.86	4.76	
V <sub>OL</sub>	Maximum LOW Level	4.5	I <sub>OUT</sub> = 50 μA	0.001	0.1	0.1	V
	Output Voltage	5.5		0.001	0.1	0.1	
		4.5	$V_{IN} = V_{IL}$ or $V_{IH}$ , $I_{OL} = 24$ mA		0.36	0.44	
		5.5	$V_{IN} = V_{IL} \text{ or } V_{IH}, I_{OL} = 24 \text{ mA}^{(4)}$		0.36	0.44	
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	$V_I = V_{CC}$ , GND		±0.1	±1.0	μΑ
l <sub>OZ</sub>	Maximum 3-STATE Leakage Current	5.5	$V_I = V_{IL}, V_{IH}; V_O = V_{CC}, GND$		±0.25	±2.5	μΑ
I <sub>CCT</sub>	Maximum I <sub>CC</sub> /Input	5.5	$V_{I} = V_{CC} - 2.1 \text{ V}$	0.6		1.5	mA
I <sub>OLD</sub>	Minimum Dynamic	5.5	V <sub>OLD</sub> = 1.65 V Max.			75	mA
I <sub>OHD</sub>	Output Current (Note 5)	5.5	V <sub>OHD</sub> = 3.85 V Min.			<del>-</del> 75	mA
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	V <sub>IN</sub> = V <sub>CC</sub> or GND		4.0	40.0	μΑ

<sup>4.</sup> All outputs loaded; thresholds on input associated with output under test.5. Maximum test duration 2.0 ms, one output loaded at a time.

# AC ELECTRICAL CHARACTERISTICS FOR AC

			T <sub>A</sub> = +2	25°C, C <sub>L</sub> =	50 pF	T <sub>A</sub> = -40°C to +8	35°C, C <sub>L</sub> = 50 pF	
Symbol	Parameter	V <sub>CC</sub> (V) (Note 6)	Min.	Тур.	Max.	Min.	Max.	Units
t <sub>PLH</sub>	Propagation Delay, Data to	3.3	2.0	5.5	8.0	1.5	9.0	ns
	Output	5.0	1.5	4.0	6.0	1.0	6.5	
t <sub>PHL</sub>	Propagation Delay, Data to	3.3	2.0	5.5	8.0	1.5	8.5	ns
	Output	5.0	1.5	4.0	6.0	1.0	6.5	
t <sub>PZH</sub>	Output Enable Time	3.3	3.0	8.0	11.5	3.0	12.5	ns
		5.0	2.0	6.0	8.5	1.5	9.5	
t <sub>PZL</sub>	Output Enable Time	3.3	2.5	7.0	10.0	2.5	11.5	ns
		5.0	1.5	5.5	7.5	1.0	8.5	
t <sub>PHZ</sub>	Output Disable Time	3.3	3.5	9.0	12.5	2.5	14.0	ns
		5.0	2.0	7.0	9.5	1.0	10.5	
t <sub>PLZ</sub>	Output Disable Time	3.3	2.5	6.5	9.5	2.0	10.5	ns
		5.0	2.0	5.5	7.5	1.0	8.5	

<sup>6.</sup> Voltage range 3.3 is 3.3 V  $\pm$  0.3 V. Voltage range 5.0 is 5.0 V  $\pm$  0.5 V.

# AC ELECTRICAL CHARACTERISTICS FOR ACT

			T <sub>A</sub> = +2	25°C, C <sub>L</sub> =	50 pF	T <sub>A</sub> = -40°C to +8	35°C, C <sub>L</sub> = 50 pF	
Symbol	Parameter	V <sub>CC</sub> (V) (Note 7)	Min.	Тур.	Max.	Min.	Max.	Units
t <sub>PLH</sub>	Propagation Delay, Data to	5.0	2.0	4.5	7.0	2.0	7.5	ns
t <sub>PHL</sub>	Output	5.0	2.0	5.5	7.0	2.0	7.5	
t <sub>PZH</sub>	Output Enable Time	5.0	2.0	5.0	9.0	2.0	9.5	ns
t <sub>PZL</sub>		5.0	2.0	6.5	9.0	2.0	9.5	
t <sub>PHZ</sub>	Output Disable Time	5.0	1.5	5.5	7.5	1.5	8.0	ns
$t_{PLZ}$		5.0	1.5	5.5	7.5	1.5	8.0	

<sup>7.</sup> Voltage range 5.0 is 5.0 V  $\pm$  0.5 V.

# CAPACITANCE

Symbol	Parameter	Conditions	Тур.	Units
C <sub>IN</sub>	Input Capacitance	V <sub>CC</sub> = OPEN	4.5	pF
C <sub>PD</sub>	Power Dissipation Capacitance for AC	V <sub>CC</sub> = 5.0 V	30.0	pF
	Power Dissipation Capacitance for ACT		70.0	

## **ORDERING INFORMATION**

Device	Device Marking	Package	Shipping <sup>†</sup>
74AC541MTCX	AC 541	TSSOP-20, case 948AQ (Pb-Free)	2500 Units / Tape & Reel
74AC541SC	AC541	SOIC-20W, case 751D (Pb-Free)	38 Units / Tube
74AC541SCX	AC541	SOIC-20W, case 751BJ (Pb-Free)	1000 Units / Tape & Reel
74ACT541MTCX	ACT 541	TSSOP-20, case 948AQ (Pb-Free)	2500 Units / Tape & Reel
74ACT541SC	ACT541	SOIC-20W, case 751D (Pb-Free)	38 Units / Tube
74ACT541SCX	ACT541	SOIC-20W, case 751BJ (Pb-Free)	1000 Units / Tape & Reel

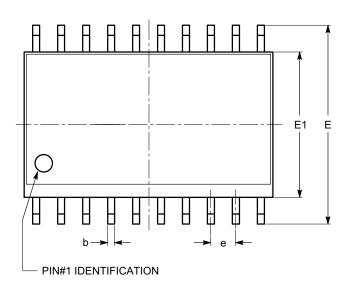
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NOTE: All packages are lead free per JEDEC: J-STD-020B standard.



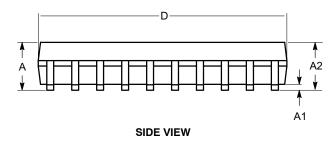
SOIC-20, 300 mils CASE 751BJ-01 ISSUE O

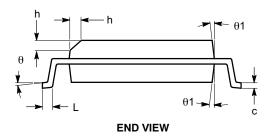
**DATE 19 DEC 2008** 



SYMBOL	MIN	NOM	MAX
Α	2.36	2.49	2.64
A1	0.10		0.30
A2	2.05		2.55
b	0.31	0.41	0.51
С	0.20	0.27	0.33
D	12.60	12.80	13.00
E	10.01	10.30	10.64
E1	7.40	7.50	7.60
е		1.27 BSC	
h	0.25		0.75
L	0.40	0.81	1.27
θ	0°		8°
θ1	5°		15°

**TOP VIEW** 





#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MS-013.

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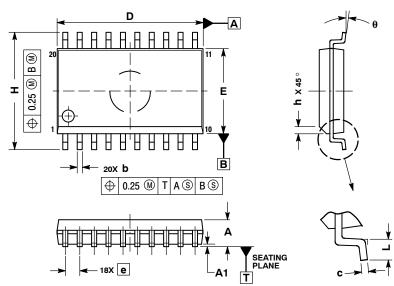




SOIC-20 WB CASE 751D-05 **ISSUE H** 

**DATE 22 APR 2015** 

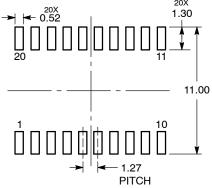
#### SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

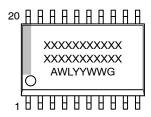
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

## RECOMMENDED **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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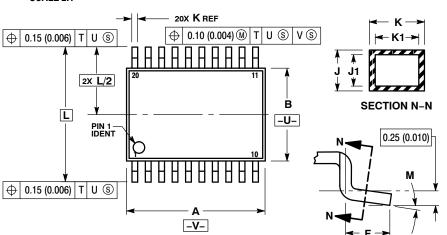
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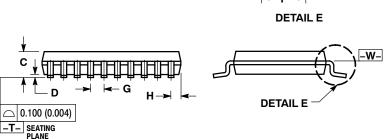
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



# TSSOP-20 WB CASE 948E ISSUE D

**DATE 17 FEB 2016** 





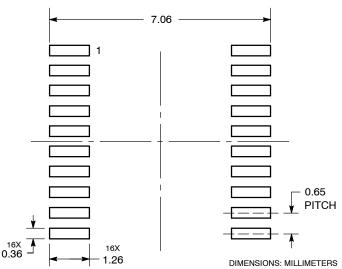
#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

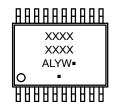
  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

#### **SOLDERING FOOTPRINT**



# **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

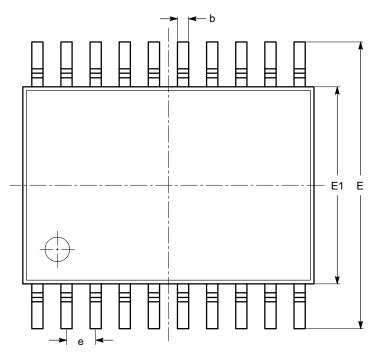
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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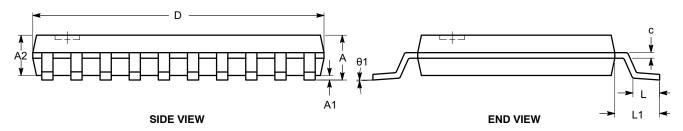
**TSSOP20, 4.4x6.5** CASE 948AQ-01 ISSUE A

**DATE 19 MAR 2009** 



SYMBOL	MIN	NOM	MAX
Α			1.20
A1	0.05		0.15
A2	0.80		1.05
b	0.19		0.30
С	0.09		0.20
D	6.40	6.50	6.60
E	6.30	6.40	6.50
E1	4.30	4.40	4.50
е		0.65 BSC	
L	0.45	0.60	0.75
L1		1.00 REF	
θ	0°		8°

**TOP VIEW** 



#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-153.

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